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**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**  
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Application Number	09/483881
Filing Date	January 18, 2000
First Named Inventor	Ahn, Kie
Group Art Unit	2812
Examiner Name	Nguyen, Ha

Sheet 1 of 1

Attorney Docket No: 303.672US1

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Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date if Appropriate
lm	US-6,120,641	10/19/2000	Stevens, E. Henry , et al.	156	345.22	08/03/1998
	US-6,277,263	08/21/2001	Chen, Linlin	205	182	08/31/1999
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	US-6,428,673	08/06/2002	Ritzdorf, Thomas L., et al.	205	84	07/08/2000
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Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T <sup>2</sup>
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**OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No *	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
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EXAMINER

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Substitute Disclosure Statement Form (PTO-1449)

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PTO/SB08A(10-01)  
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US Patent & Trademark Office: U.S. DEPARTMENT OF COMMERCE

Complete if Known

Application Number	09/483881
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First Named Inventor	Ahn, Kie
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Examiner Name	Nguyen, Ha

Attorney Docket No: 303.672US1

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Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
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	US-2,244,608	06/03/1941	Cooper, H. S.	75	138	02/09/1939
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	US-4,857,481	08/15/1989	Tam, G. , et al.	437	182	03/14/1989

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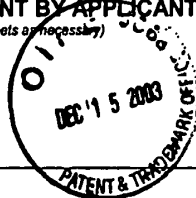
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Substitute Disclosure Statement Form (PTO-1449)

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Application Number	09/483881
Filing Date	January 18, 2000
First Named Inventor	Ahn, Kie
Group Art Unit	2812
Examiner Name	Nguyen, Ha

Attorney Docket No: 303.672US1

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<b>Application Number</b>	09/483881
<b>Filing Date</b>	January 18, 2000
<b>First Named Inventor</b>	Ahn, Kie
<b>Group Art Unit</b>	2812
<b>Examiner Name</b>	Nguyen, Ha

Sheet 3 of 7

Attorney Docket No: 303.672US1

in	US-5,534,731	07/09/1996	Cheung, Robin	257	759	10/28/1994
	US-5,538,922	07/23/1996	Cooper, K J., et al.	437	195	01/25/1995
	US-5,539,060	07/23/1996	Tsunogae, Y., et al.	525	338	10/13/1995
	US-5,539,227	07/23/1996	Nakano, H.	257	276	08/02/1995
	US-5,578,146	11/26/1996	Grant, L. A., et al.	148	437	01/16/1996
	US-5,625,232	04/29/1997	Numata, K., et al.	257	758	07/15/1994
	US-5,635,253	06/03/1997	Canaperi, Donald F., et al.	427	437	06/07/1995
	US-5,662,788	09/02/1997	Sandhu, G., et al.	205	87	06/03/1996
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	US-5,674,787	10/07/1997	Zhao, Bin, et al.	437	230	01/16/1996
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	US-5,679,608	10/21/1997	Cheung, Robin W., et al.	437	195	06/05/1995
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	US-5,695,810	12/09/1997	Dubin, Valery M., et al.	427	96	11/20/1996
	US-5,705,425	01/06/1998	Miura, T., et al.	437	182	04/26/1996
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	US-5,780,358	07/14/1998	Zhou, M. S.	438	645	04/08/1996
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	US-5,792,522	08/11/1998	Jin, S., et al.	427	575	09/18/1996
	US-5,792,706	08/11/1998	Michael, M. W., et al.	438	626	06/05/1996
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	US-5,852,871	12/29/1998	Khandros, I. Y.	29	843	12/11/1995
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	US-5,969,422	10/19/1999	Ting, C., et al.	257	762	05/15/1997
✓	US-5,972,804	10/26/1999	Tobin, Philip J., et al.	438	786	11/03/1997
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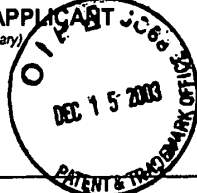
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Attorney Docket No: 303.672US1	

Sheet 4 of 7

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	US-6,075,278	06/13/2000	Farrar, P. A.	257	522	04/24/1997
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	US-6,091,136	07/18/2000	Jiang, T., et al.	257	676	11/17/1998
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	US-6,208,016	03/27/2001	Farrar, Paul	257	643	02/24/1999
	US-6,211,561	04/03/2001	Zhao, B	257	522	11/16/1998
	US-6,214,719	04/10/2001	Nag, Somnath	438	619	09/30/1999
	US-6,218,282	04/17/2001	Buynoski, M. S.	438	619	02/18/1999
	US-6,245,658	06/12/2001	Buynoski, M.	438	619	02/18/1999
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	US-6,288,905	09/11/2001	Chung, K. K.	361	771	10/04/1999
	US-6,323,543	11/27/2001	Jiang, T., et al.	257	676	04/13/2000
	US-6,329,279	12/11/2001	Lee, R	438	619	03/24/2000
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	US-6,383,920	05/07/2002	Wang, P., et al.	438	639	01/10/2001
✓	US-6,563,219	05/13/2003	Ireland, Phillip, et al.	257	758	11/02/2001

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	First Named Inventor	Ahn, Kie
	Group Art Unit	2812
	Examiner Name	Nguyen, Ha
Sheet 5 of 7	Attorney Docket No: 303.672US1	

FOREIGN PATENT DOCUMENTS					
Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass

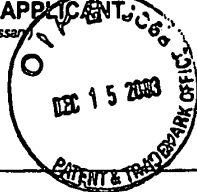
OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS					
Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.			T <sup>2</sup>
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		Application Number	09/483881
		Filing Date	January 18, 2000
		First Named Inventor	Ahn, Kie
		Group Art Unit	2812
		Examiner Name	Nguyen, Ha
Sheet 6 of 7		Attorney Docket No: 303.672US1	

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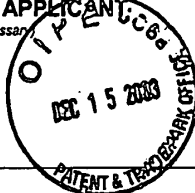
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Application Number	09/483881
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Examiner Name	Nguyen, Ha

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lm		SHIEH, B. , et al., "Air-Gap Formation During IMD Deposition to Lower Interconnect Capacitance", <u>IEEE Electron Device Letters</u> , 19(1), (1998),16-18	
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